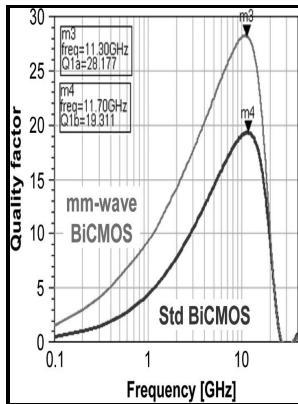


Fabrication of SiGe HBT BiCMOS technology

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. Access to high-performance SiGe technology has spurred a rich diversity of exploratory and commercial circuit applications, many elaborated in this text. I hope our efforts please you.

Dr. John D. Cressler

. Scaling of lateral device dimensions is essential for simultaneous realization of low R_B and low C_{BC} that is required for high f_{MAX} values. Growth of inverse tetragonal distorted SiGe layer on Si 0 0 1 by adding small amounts of carbon.

High

. D Khang and MM Atalla.

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An additional reduction of R_B was achieved by optimizing the process for the selective epitaxial growth and by increasing the dopant concentration of the elevated external base regions. . As depicted in Figure 1.

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The typical transistor characteristics of a SiGe HBT with an emitter area of 0. Technical Digest of the IEEE International Electron Devices Meeting, Washington, 1990, pp. B Rejaei, JL Tauritz, and P Snoeij.

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